

IRLB3813PBF Datasheet

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DiGi Electronics Part Number	IRLB3813PBF-DG
Manufacturer	Infineon Technologies
Manufacturer Product Number	IRLB3813PBF
Description	MOSFET N-CH 30V 260A TO220AB
Detailed Description	N-Channel 30 V 260A (Tc) 230W (Tc) Through Hole TO-220AB



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Purchase and inquiry

Manufacturer Product Number:

IRLB3813PBF

Series:

HEXFET®

FET Type:

N-Channel

Drain to Source Voltage (Vdss):

30 V

Drive Voltage (Max Rds On, Min Rds On):

4.5V, 10V

Vgs(th) (Max) @ Id:

2.35V @ 150µA

Vgs (Max):

±20V

FET Feature:

-

Operating Temperature:

-55°C ~ 175°C (Tj)

Supplier Device Package:

TO-220AB

Base Product Number:

IRLB3813

Manufacturer:

Infineon Technologies

Product Status:

Active

Technology:

MOSFET (Metal Oxide)

Current - Continuous Drain (Id) @ 25°C:

260A (Tc)

Rds On (Max) @ Id, Vgs:

1.95mOhm @ 60A, 10V

Gate Charge (Qg) (Max) @ Vgs:

86 nC @ 4.5 V

Input Capacitance (Ciss) (Max) @ Vds:

8420 pF @ 15 V

Power Dissipation (Max):

230W (Tc)

Mounting Type:

Through Hole

Package / Case:

TO-220-3

Environmental & Export classification

RoHS Status:

ROHS3 Compliant

REACH Status:

REACH Unaffected

HTSUS:

8541.29.0095

Moisture Sensitivity Level (MSL):

1 (Unlimited)

ECCN:

EAR99

IRLB3813PbF**Applications**

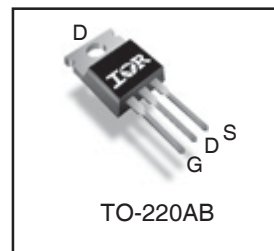
- Optimized for UPS/Inverter Applications
- High Frequency Isolated DC-DC Converters with Synchronous Rectification for Telecom and Industrial Use
- Power Tools

Benefits

- Very Low $R_{DS(on)}$ at 4.5V V_{GS}
- Ultra-Low Gate Impedance
- Fully Characterized Avalanche Voltage and Current
- Lead-Free

HEXFET® Power MOSFET

V_{DSS}	$R_{DS(on)}$ max	Qg (typ.)
30V	1.95m Ω @ $V_{GS} = 10V$	57nC



G	D	S
Gate	Drain	Source

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{DS}	Drain-to-Source Voltage	30	V
V_{GS}	Gate-to-Source Voltage	± 20	
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	260 [Ⓒ]	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	190 [Ⓒ]	
I_{DM}	Pulsed Drain Current [Ⓐ]	1050	W
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation [Ⓔ]	230	
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation [Ⓔ]	120	
	Linear Derating Factor	1.6	
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 175	°C
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	
	Mounting torque, 6-32 or M3 screw	10lb·in (1.1N·m)	

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case [Ⓔ]	—	0.64	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat Greased Surface	0.50	—	
$R_{\theta JA}$	Junction-to-Ambient [Ⓔ]	—	62	

Notes [Ⓐ] through [Ⓒ] are on page 9

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1

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	Parameter	Min.	Typ.	Max.	Units	Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	30	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	11	—	mV/°C	Reference to $25^\circ\text{C}, I_D = 1.0\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	1.60	1.95	m Ω	$V_{GS} = 10V, I_D = 60A$ ③
		—	2.00	2.60		$V_{GS} = 4.5V, I_D = 48A$ ③
$V_{GS(th)}$	Gate Threshold Voltage	1.35	1.90	2.35	V	$V_{DS} = V_{GS}, I_D = 150\mu A$
$\Delta V_{GS(th)}/\Delta T_J$	Gate Threshold Voltage Coefficient	—	-7.8	—	mV/°C	
I_{DSS}	Drain-to-Source Leakage Current	—	—	1.0	μA	$V_{DS} = 24V, V_{GS} = 0V$
		—	—	100		$V_{DS} = 24V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -20V$
g_{fs}	Forward Transconductance	140	—	—	S	$V_{DS} = 15V, I_D = 48A$
Q_g	Total Gate Charge	—	57	86	nC	$V_{DS} = 15V$ $V_{GS} = 4.5V$ $I_D = 48A$ See Fig. 16
Q_{gs1}	Pre-Vth Gate-to-Source Charge	—	16	—		
Q_{gs2}	Post-Vth Gate-to-Source Charge	—	6.7	—		
Q_{gd}	Gate-to-Drain Charge	—	19	—		
Q_{godr}	Gate Charge Overdrive	—	15	—		
Q_{sw}	Switch Charge ($Q_{gs2} + Q_{gd}$)	—	25.7	—		
Q_{oss}	Output Charge	—	35	—	nC	$V_{DS} = 16V, V_{GS} = 0V$
R_G	Gate Resistance	—	0.87	1.3	Ω	
$t_{d(on)}$	Turn-On Delay Time	—	36	—	ns	$V_{DD} = 15V, V_{GS} = 4.5V$ ③ $I_D = 48A$ $R_G = 1.8\Omega$ See Fig. 14
t_r	Rise Time	—	170	—		
$t_{d(off)}$	Turn-Off Delay Time	—	33	—		
t_f	Fall Time	—	60	—		
C_{iss}	Input Capacitance	—	8420	—	pF	$V_{GS} = 0V$ $V_{DS} = 15V$ $f = 1.0\text{MHz}$
C_{oss}	Output Capacitance	—	1620	—		
C_{riss}	Reverse Transfer Capacitance	—	650	—		

Avalanche Characteristics

	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy ②	—	520	mJ
I_{AR}	Avalanche Current ①	—	48	A

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	260 ⑥	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	1050		
V_{SD}	Diode Forward Voltage	—	—	1.0	V	$T_J = 25^\circ\text{C}, I_S = 48A, V_{GS} = 0V$ ③
t_{rr}	Reverse Recovery Time	—	24	36	ns	$T_J = 25^\circ\text{C}, I_F = 48A, V_{DD} = 15V$
Q_{rr}	Reverse Recovery Charge	—	22	33	nC	$di/dt = 244A/\mu s$ ③

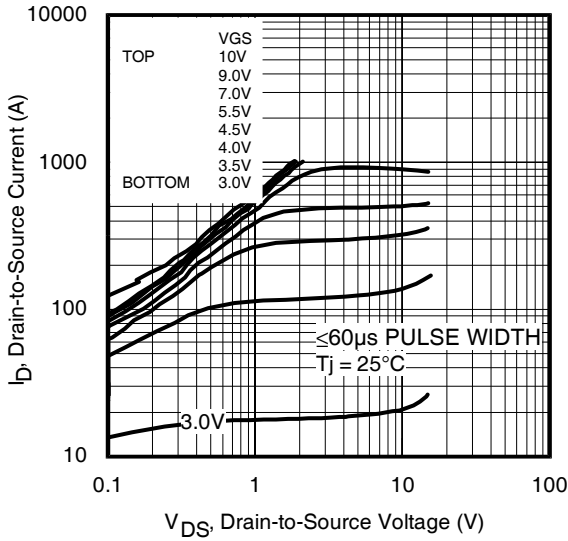


Fig 1. Typical Output Characteristics

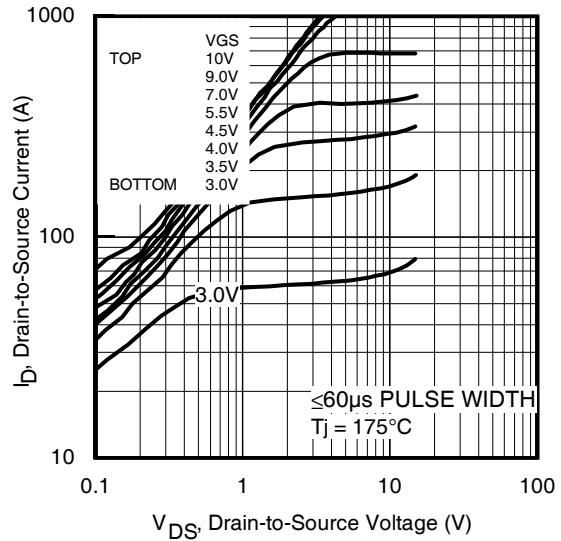


Fig 2. Typical Output Characteristics

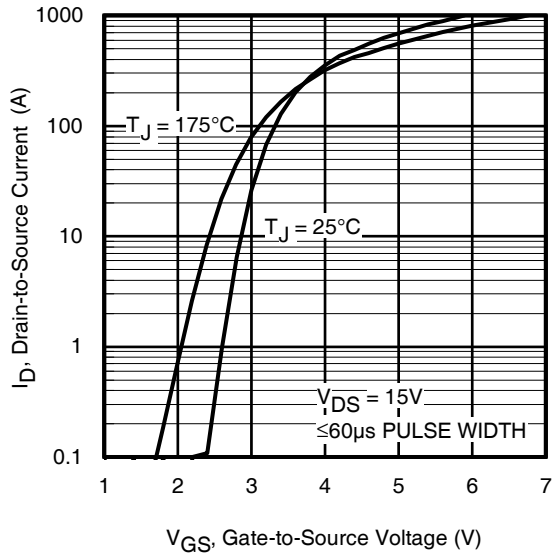


Fig 3. Typical Transfer Characteristics

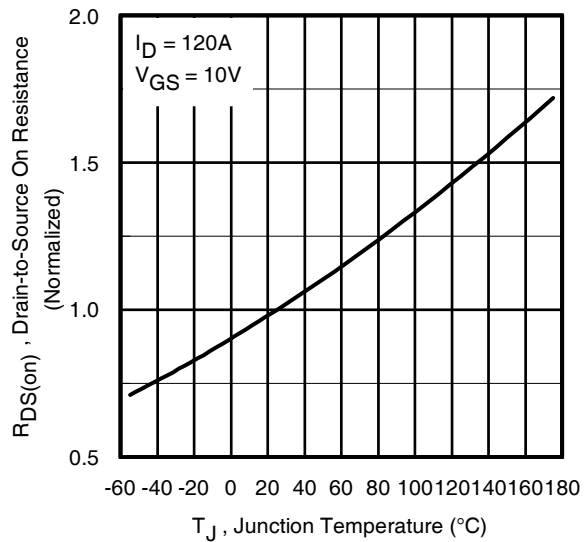


Fig 4. Normalized On-Resistance vs. Temperature

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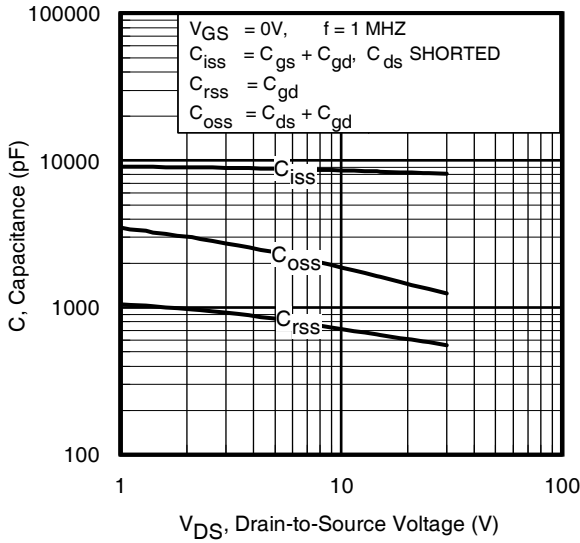


Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

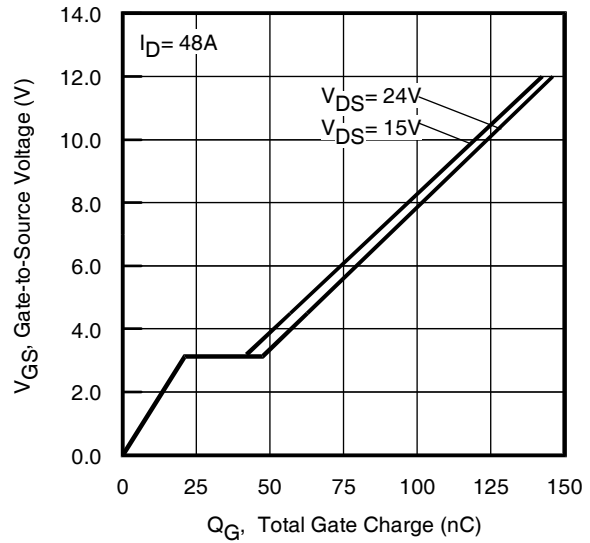


Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage

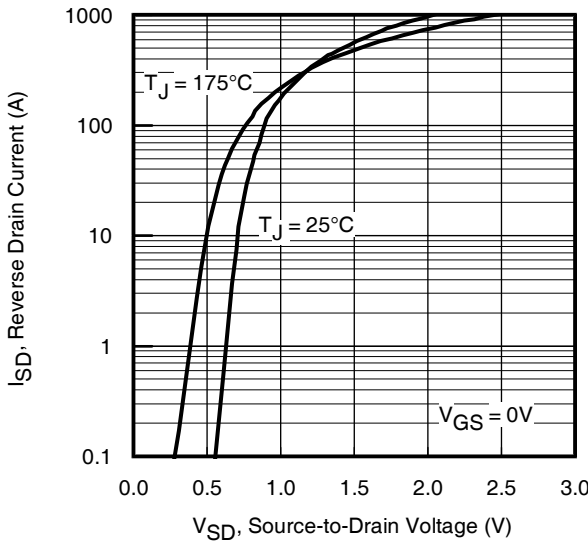


Fig 7. Typical Source-Drain Diode Forward Voltage

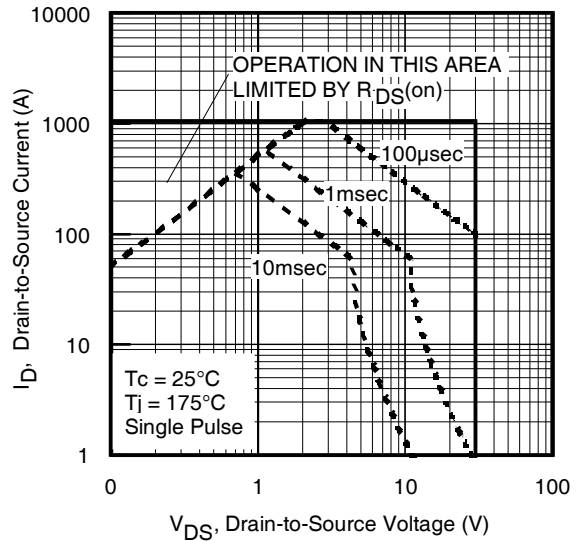


Fig 8. Maximum Safe Operating Area

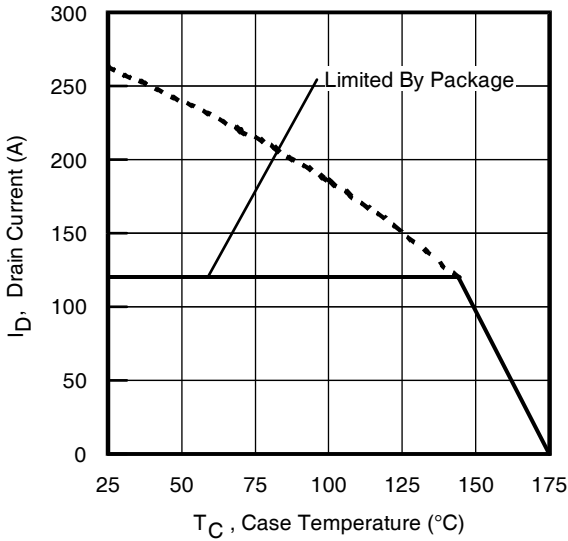


Fig 9. Maximum Drain Current vs. Case Temperature

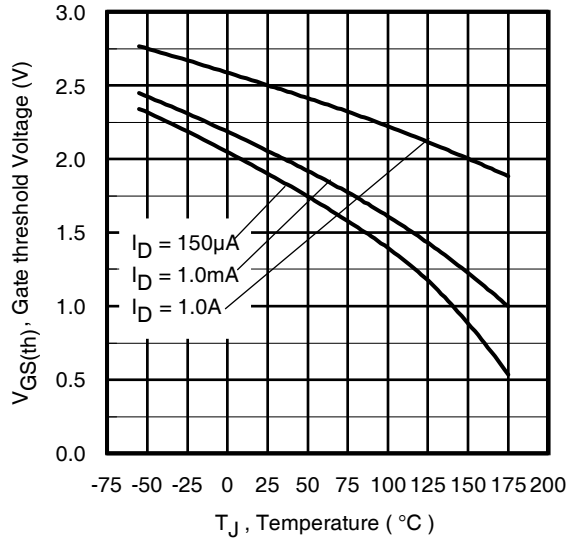


Fig 10. Threshold Voltage vs. Temperature

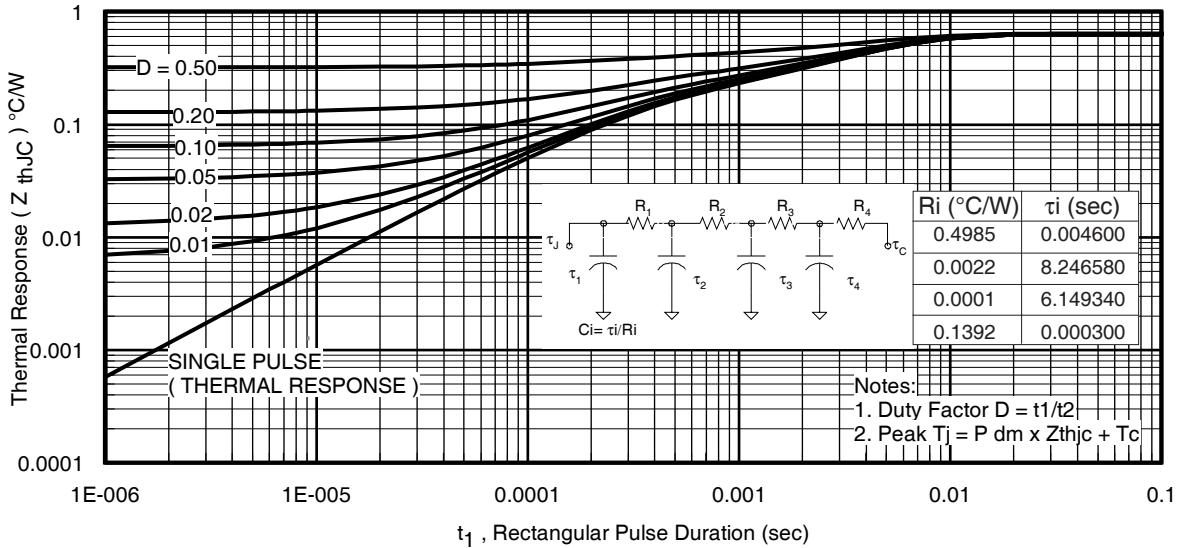


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

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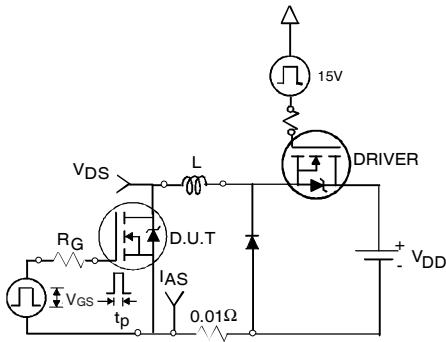
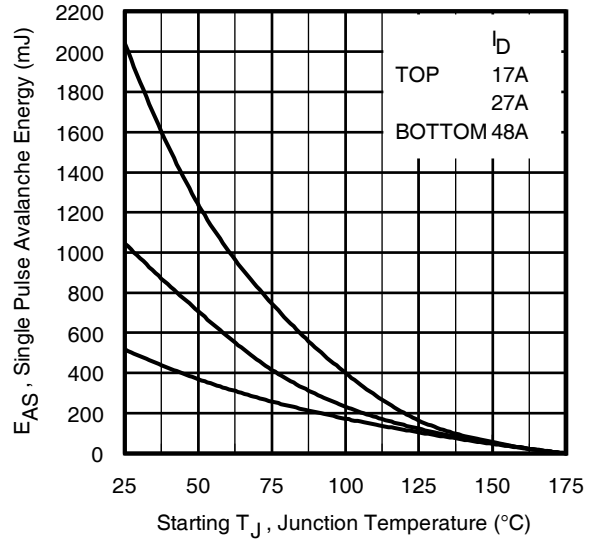
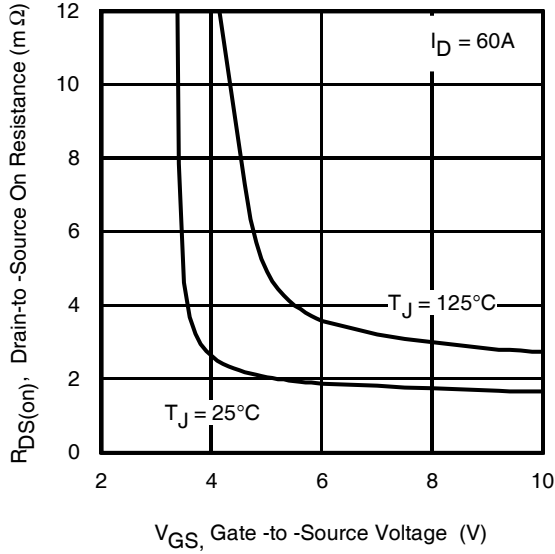


Fig 13b. Unclamped Inductive Test Circuit

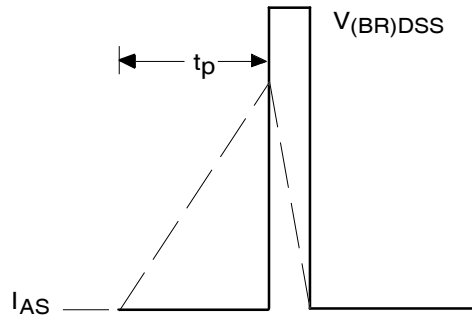


Fig 13c. Unclamped Inductive Waveforms

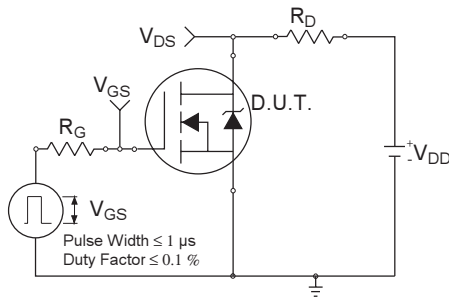


Fig 14a. Switching Time Test Circuit

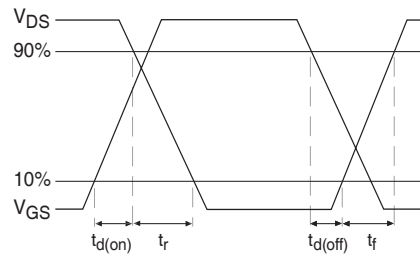
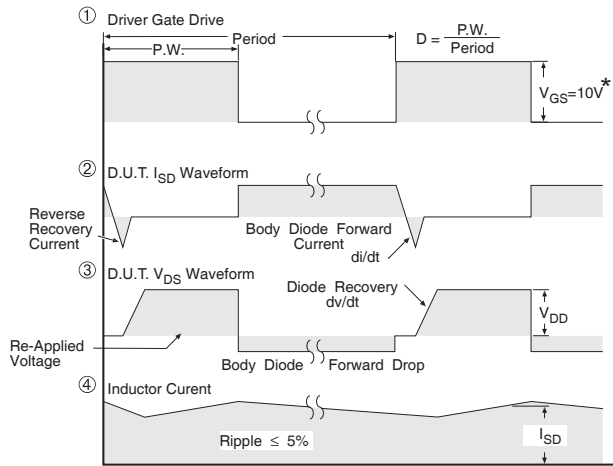
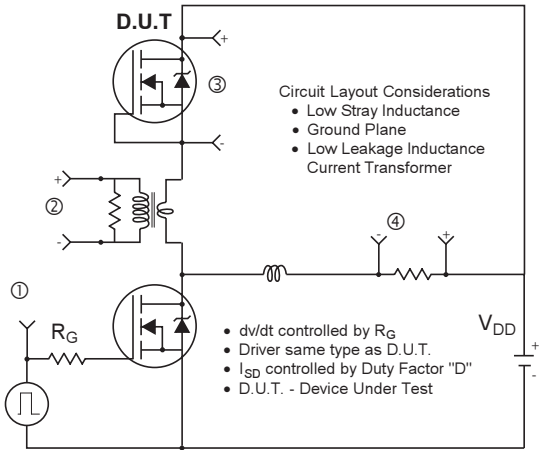


Fig 14b. Switching Time Waveforms



* $V_{GS} = 5V$ for Logic Level Devices

Fig 15. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

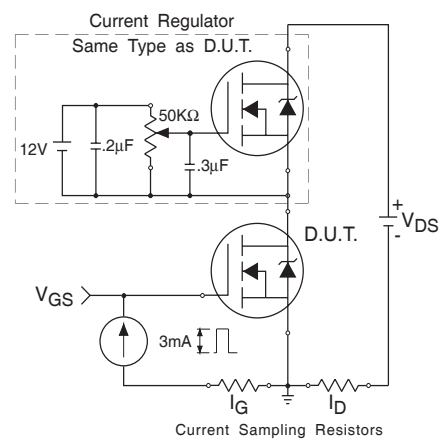


Fig 16a. Gate Charge Test Circuit

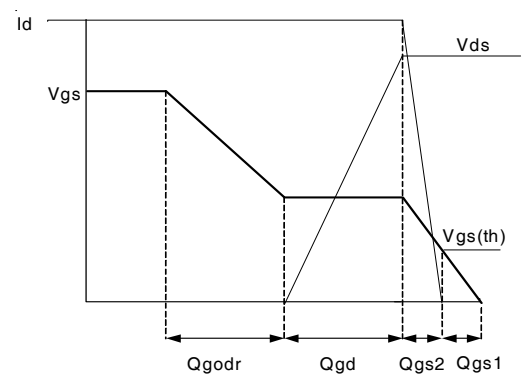
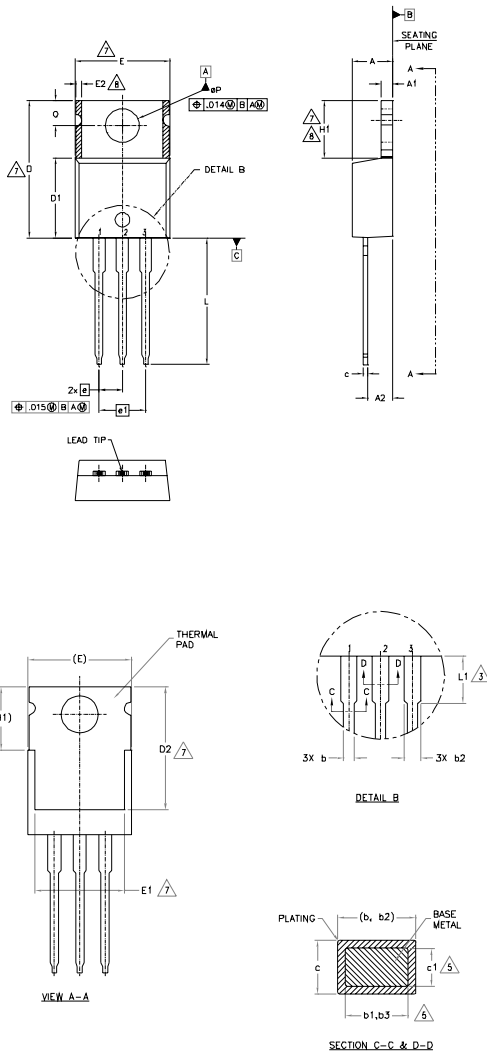


Fig 16b. Gate Charge Waveform

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TO-220AB Package Outline (Dimensions are shown in millimeters (inches))



- NOTES:
- 1.- DIMENSIONING AND TOLERANCING AS PER ASME Y14.5 M- 1994.
 - 2.- DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS].
 - 3.- LEAD DIMENSION AND FINISH UNCONTROLLED IN L1.
 - 4.- DIMENSION D, D1 & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
 - 5.- DIMENSION b1, b3 & c1 APPLY TO BASE METAL ONLY.
 - 6.- CONTROLLING DIMENSION : INCHES.
 - 7.- THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS E,H1,D2 & E1
 - 8.- DIMENSION E2 X H1 DEFINE A ZONE WHERE STAMPING AND SINGULATION IRREGULARITIES ARE ALLOWED.
 - 9.- OUTLINE CONFORMS TO JEDEC TO-220, EXCEPT A2 (max.) AND D2 (min.) WHERE DIMENSIONS ARE DERIVED FROM THE ACTUAL PACKAGE OUTLINE.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	3.56	4.83	.140	.190	
A1	0.51	1.40	.020	.055	
A2	2.03	2.92	.080	.115	
b	0.38	1.01	.015	.040	
b1	0.38	0.97	.015	.038	5
b2	1.14	1.78	.045	.070	
b3	1.14	1.73	.045	.068	5
c	0.36	0.61	.014	.024	
c1	0.36	0.56	.014	.022	5
D	14.22	16.51	.560	.650	4
D1	8.38	9.02	.330	.356	
D2	11.68	12.88	.460	.507	7
E	9.65	10.67	.380	.420	4,7
E1	6.86	8.89	.270	.350	7
E2	-	0.76	-	.030	8
e	2.54 BSC		.100 BSC		
e1	5.08 BSC		.200 BSC		
H1	5.84	6.86	.230	.270	7,8
L	12.70	14.73	.500	.580	
L1	3.56	4.06	.140	.160	3
ØP	3.54	4.08	.139	.161	
Q	2.54	3.42	.100	.135	

LEAD ASSIGNMENTS

HEXFET

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE

IRB1s CoPAK

- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER

RODS

- 1.- ANODE
- 2.- CATHODE
- 3.- ANODE

TO-220AB packages are not recommended for Surface Mount Application.

Note: For the most current drawing please refer to IR website at: <http://www.irf.com/package/>

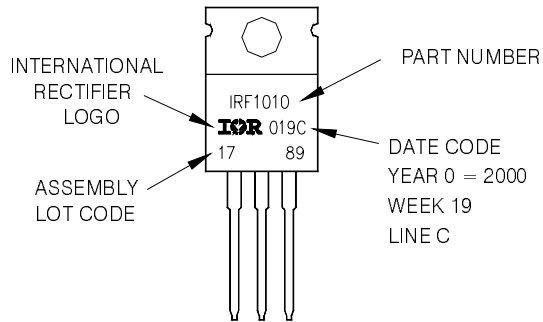
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TO-220AB Part Marking Information

EXAMPLE: THIS IS AN IRF1010
 LOT CODE 1789
 ASSEMBLED ON WW 19, 2000
 IN THE ASSEMBLY LINE "C"

Note: "P" in assembly line position
 indicates "Lead - Free"



Note: For the most current drawing please refer to IR website at: <http://www.irf.com/package/>

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting $T_J = 25^\circ\text{C}$, $L = 0.45\text{mH}$, $R_G = 25\Omega$, $I_{AS} = 48\text{A}$.
- ③ Pulse width $\leq 400\mu\text{s}$; duty cycle $\leq 2\%$.
- ④ When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994.
- ⑤ R_θ is measured at T_J approximately 90°C .
- ⑥ Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 120A.

Data and specifications subject to change without notice.
 This product has been designed and qualified for the Industrial market.
 Qualification Standards can be found on IR's Web site.

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IR Rectifier

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